

### FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Volt Drop
- Isolated Cu Base with Al<sub>2</sub>O<sub>3</sub> Substrates
- Dual Diodes can be paralleled for 1800A Rating
- Lead Free Construction

### APPLICATIONS

- Chopper Diodes
- Boost and Buck Circuits
- Free-wheel Circuits
- Multi-level Switch Inverters

The DFM900FXS12-A000 is a dual 1200V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

### ORDERING INFORMATION

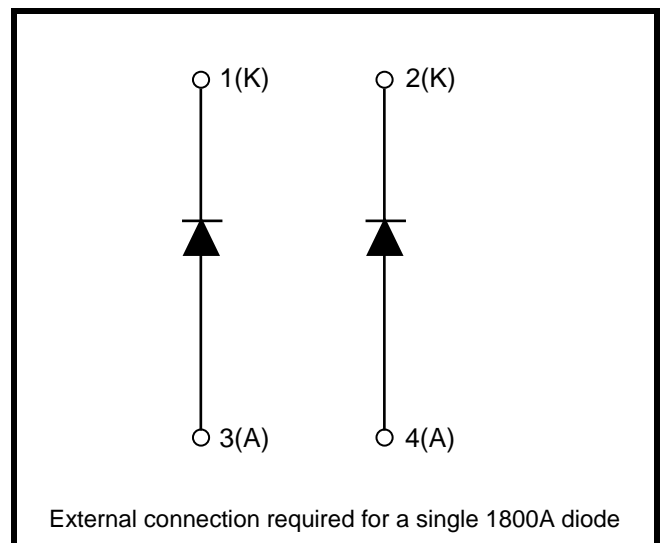
Order As:

#### DFM900FXS12-A000

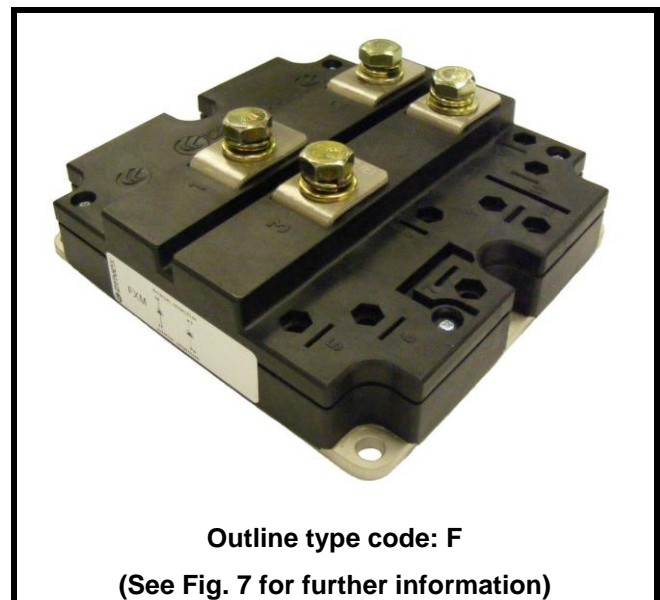
Note: When ordering, please use the complete part number

### KEY PARAMETERS

$V_{RRM}$		<b>1200V</b>
$V_F$	(typ)	<b>1.9V</b>
$I_F$	(max)	<b>900A</b>
$I_{FM}$	(max)	<b>1800A</b>



**Fig. 1 Circuit configuration**



**Fig. 2 Package**

**ABSOLUTE MAXIMUM RATINGS**

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{\text{case}} = 25^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
$V_{\text{RRM}}$	Repetitive peak reverse voltage	$T_j = 125^{\circ}\text{C}$	1200	V
$I_{\text{F}}$	Forward current (per arm)	DC, $T_{\text{case}} = 75^{\circ}\text{C}$ , $T_j = 125^{\circ}\text{C}$	900	A
$I_{\text{FM}}$	Max. forward current	$T_{\text{case}} = 110^{\circ}\text{C}$ , $t_p = 1\text{ms}$	1800	A
$I^2t$	$I^2t$ value fuse current rating	$V_R = 0$ , $t_p = 10\text{ms}$ , $T_j = 125^{\circ}\text{C}$	150	$\text{kA}^2\text{s}$
$P_{\text{max}}$	Max. transistor power dissipation	$T_{\text{case}} = 25^{\circ}\text{C}$ , $T_j = 125^{\circ}\text{C}$	2700	W
$V_{\text{isol}}$	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V

**THERMAL AND MECHANICAL RATINGS**

Internal insulation material:	$\text{Al}_2\text{O}_3$
Baseplate material:	Cu
Creepage distance:	20mm
Clearance:	10mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{\text{th}(j-c)}$	Thermal resistance (per arm)	Continuous dissipation – junction to case	-	-	27	$^{\circ}\text{C}/\text{kW}$
$R_{\text{th}(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
$T_j$	Junction temperature		-	-	125	$^{\circ}\text{C}$
$T_{\text{stg}}$	Storage temperature range		-40	-	125	$^{\circ}\text{C}$
	Screw Torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M8	-	-	10	Nm

## STATIC ELECTRICAL CHARACTERISTICS – PER ARM

 $T_{case} = 25^{\circ}\text{C}$  unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$I_{RM}$	Peak reverse current	$V_R = 1200\text{V}$ , $T_j = 125^{\circ}\text{C}$			22.5	mA
$V_F$	Forward voltage	$I_F = 900\text{A}$		1.9	2.2	V
		$I_F = 900\text{A}$ , $T_j = 125^{\circ}\text{C}$		2.1	2.4	V
$L_M$	Inductance			20		nH

## STATIC ELECTRICAL CHARACTERISTICS

 $T_{case} = 25^{\circ}\text{C}$  unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$L_M$	Module inductance (externally connected in parallel)			15		nH

## DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM

 $T_{case} = 25^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$Q_{rr}$	Reverse recovery charge	$I_F = 900\text{A}$ $V_R = 600\text{V}$ $di_F/dt = 7000\text{A}/\mu\text{s}$		150		$\mu\text{C}$
$I_{rr}$	Peak reverse recovery current			600		A
$E_{rec}$	Reverse recovery energy			60		mJ

 $T_{case} = 125^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$Q_{rr}$	Reverse recovery charge	$I_F = 900\text{A}$ $V_R = 600\text{V}$ $di_F/dt = 6300\text{A}/\mu\text{s}$		220		$\mu\text{C}$
$I_{rr}$	Peak reverse recovery current			720		A
$E_{rec}$	Reverse recovery energy			105		mJ

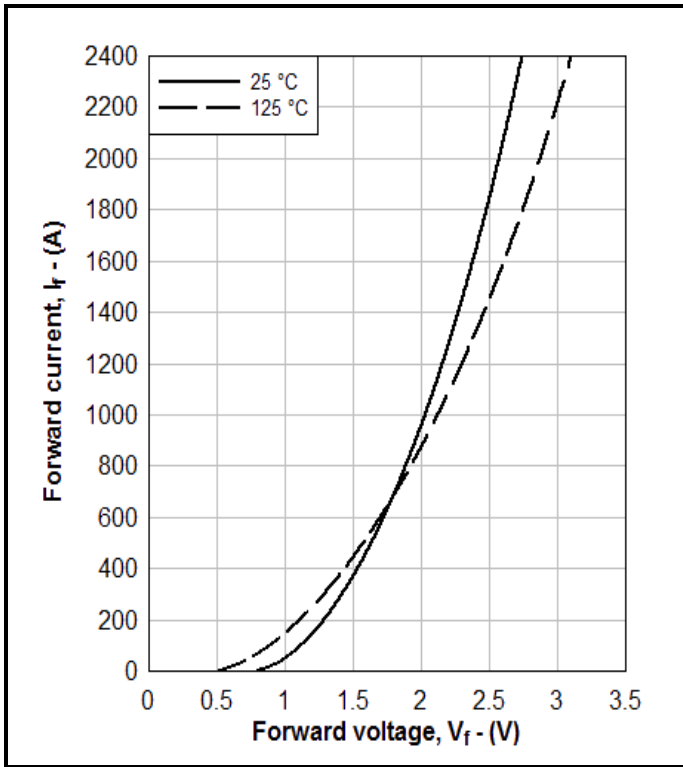


Fig. 3 Diode typical forward characteristics

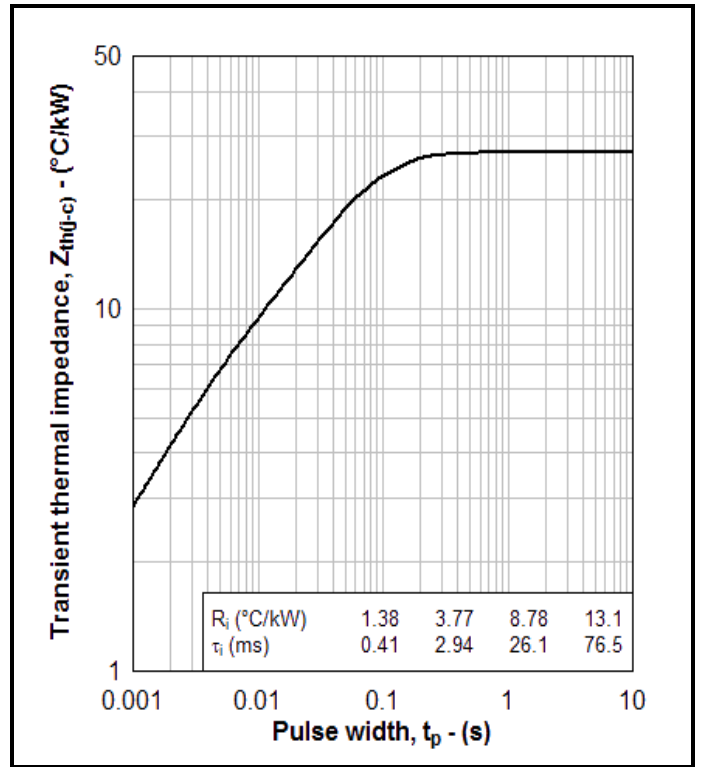


Fig. 4 Transient thermal impedance

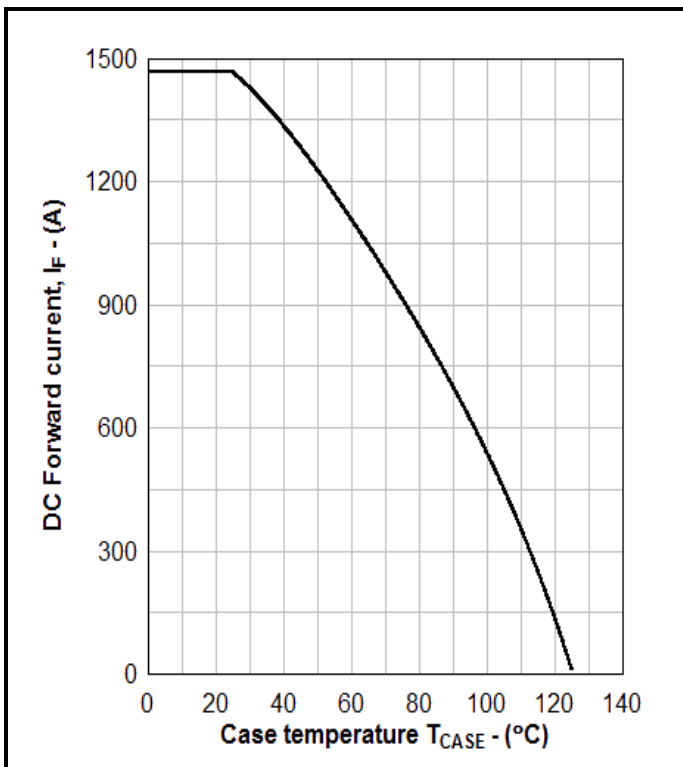


Fig. 5 DC Current rating vs case temperature

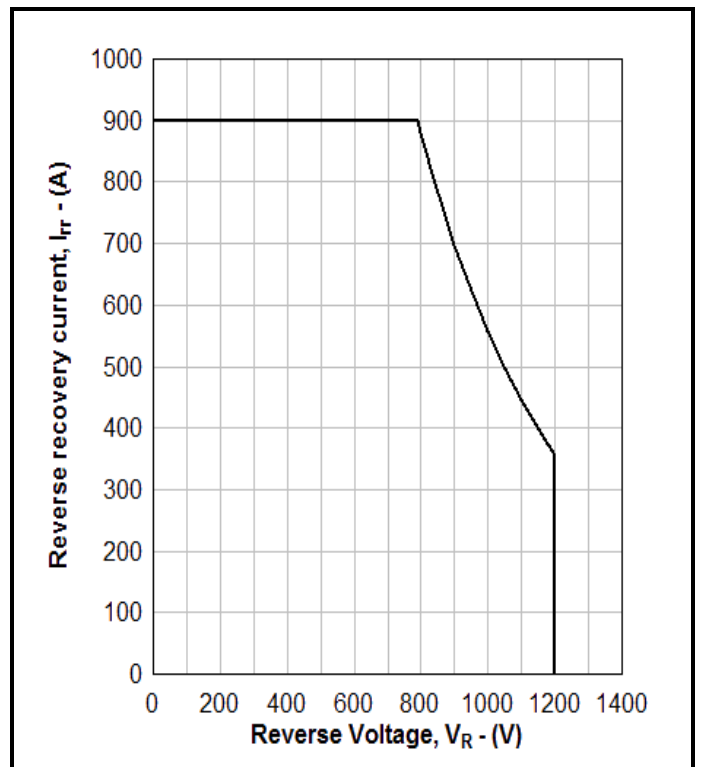
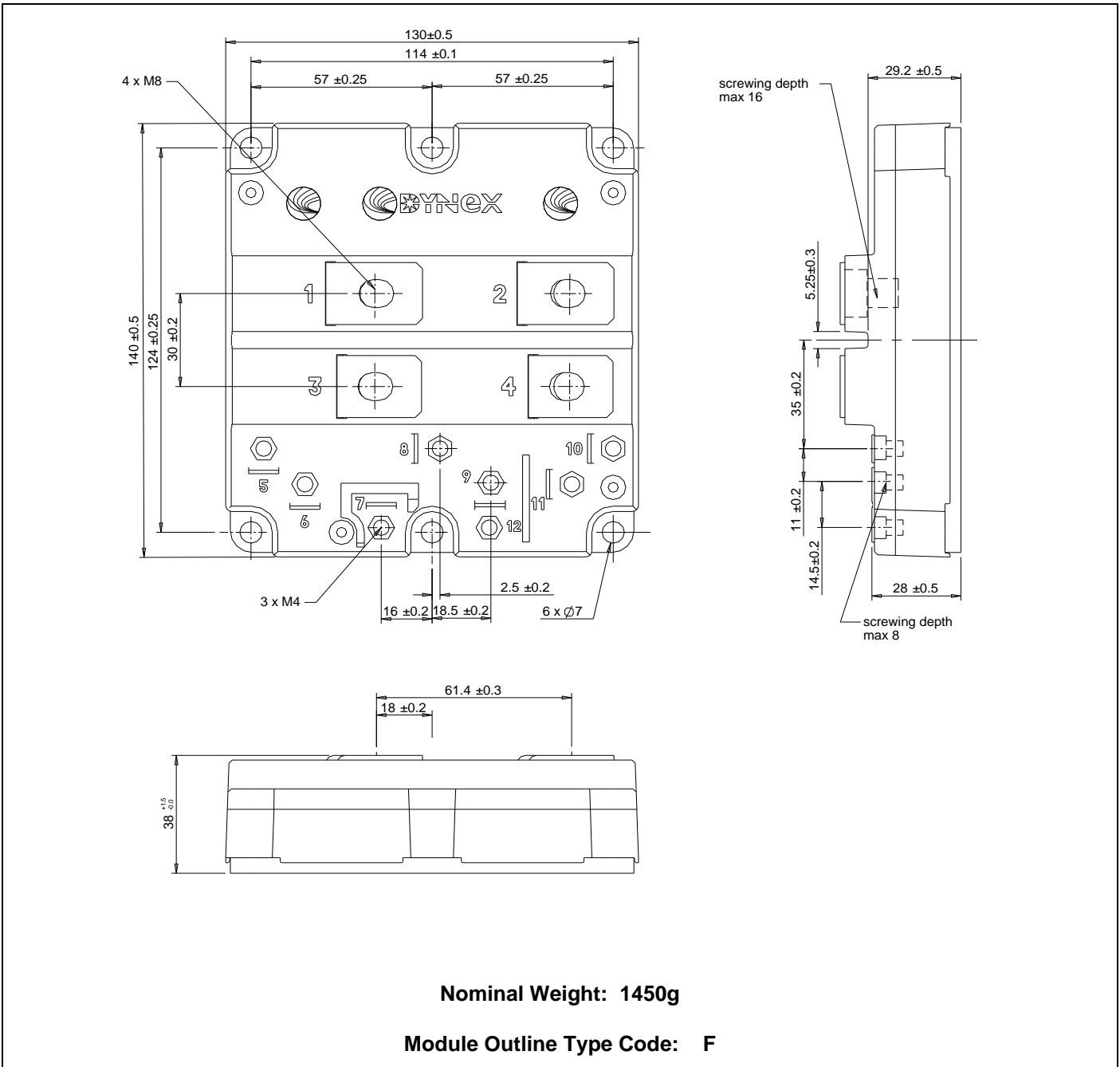


Fig. 6 RBSOA

**PACKAGE DETAILS**

For further package information, please visit our website or contact Customer Services.  
 All dimensions in mm, unless stated otherwise.  
**DO NOT SCALE.**



**Nominal Weight: 1450g**

**Module Outline Type Code: F**

**Fig. 7 Module outline drawing**

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